

# VE 320 Summer 2019

## Introduction to Semiconductor Devices

Instructor: Rui Yang (杨睿)

Office: JI Building 434

[rui.yang@sjtu.edu.cn](mailto:rui.yang@sjtu.edu.cn)



# Lecture 1

## Information session & Introduction to solids and crystal structures (Chapter 1)

# About the instructor

- 2011.08 – 2016.05. Ph.D., Electrical Engineering, Case Western Reserve University

- TA of three courses



- 2016.07 – 2018.07. Postdoc Fellow, Electrical Engineering, Stanford University



- 2018.08 – present. Assistant Professor, UM-SJTU Joint Institute, Shanghai Jiao Tong University, Shanghai, China

- Instructor of VE215



# Course schedule

- Lectures: Monday 10:00 – 11:40 am  
Wednesday 10:00 – 11:40 am  
Friday 10:00 – 11:40 am (even weeks)
- Recitation: TBD
- Location: Dong Shang Yuan (D) Room 111
- My office hours: Mo & We 1:30 – 2:30 pm, Rm. 434, UM-SJTU JI Building
- Prerequisites: Ve215, Vp240(or Vp260)
  - If you do not meet this requirement, please see the instructor immediately after class
- TA:
  - Yijin Rui (芮意进), [iregion@sjtu.edu.cn](mailto:iregion@sjtu.edu.cn)
  - Sheng Shen (申晟), [shensheng97@sjtu.edu.cn](mailto:shensheng97@sjtu.edu.cn)

# Instructor's contact

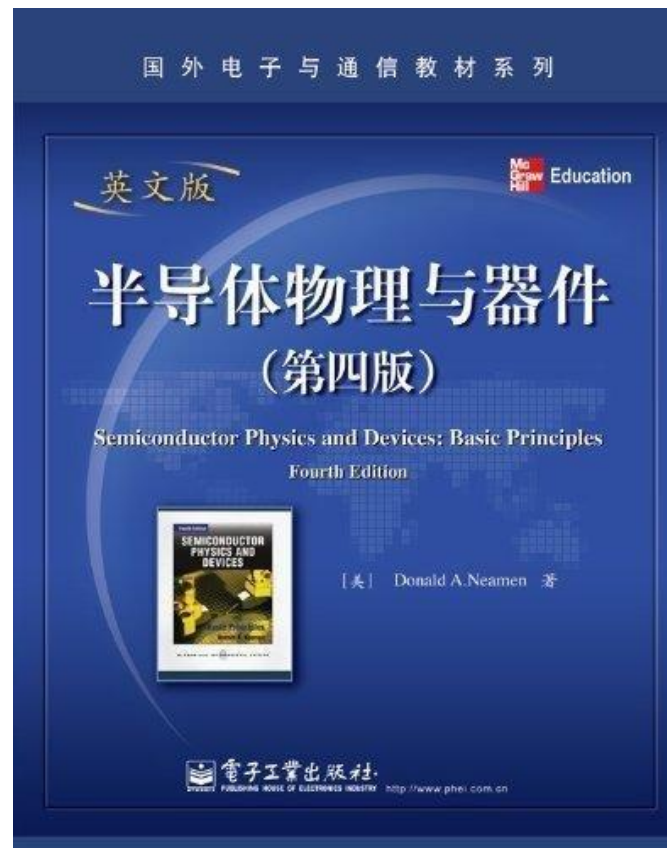
- Office location:  
Rm. 434, UM-SJTU JI Building
- Office tel:  
3420-8540 ext. 4341
- Email:  
[rui.yang@sjtu.edu.cn](mailto:rui.yang@sjtu.edu.cn)

# Textbook 1

Semiconductor Physics and Devices: Basic Principles 4<sup>th</sup> ed.

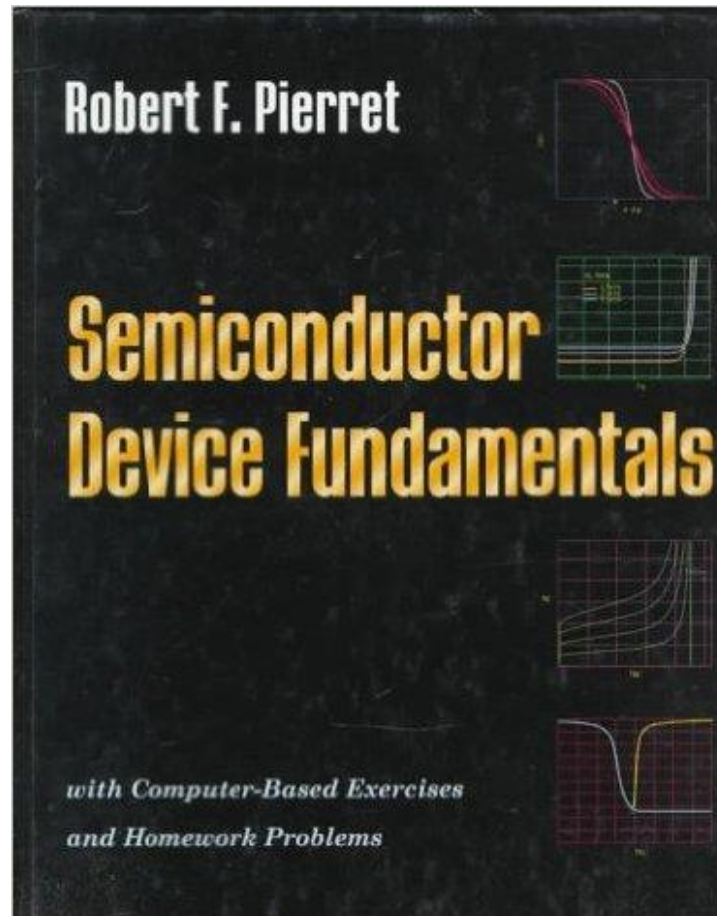
Donald A. Neamen

Publishing house of electronic industry



# Textbook 2

Semiconductor Device Fundamentals, 2<sup>nd</sup> Ed.  
Robert F. Pierret, (available JI library)



# Grading policy

- Ve320 has 10 problem sets (homework assignments), and 3 exams
- Random in-class quizzes: 5%
- Problem sets: 5%
- Exam 1(Midterm Exam 1): 30%
- Exam 2(Midterm Exam 2): 30%
- Exam 3(Final Exam): 30%
- Curve to be centered at B or B+



# The JI Honor Code

- Personal integrity as students and professionals.
- Respect other people and their work.
- Respect yourself and your own efforts.
- Mutual trust.
- Applicable to all your academic activities here, including homework, quizzes, lab reports, projects and exams.
- Violations will be reported to the Honor Council.
  - Copy other student's homework, quizzes, lab reports, exams.
  - Illegal copy of online resource and academic literatures.
  - Helping others on the abovementioned activities.
  - Fake ID for exams.

# Class rules

- Please do not come in late and do not get up to leave until the class is dismissed.
- You are responsible for all material covered in class, whether or not it is in the book.
- Read the book after the class.
- Problem sets (homework assignments) may be discussed with partners, but the work you submit must be your own.
- Homework will be assigned online at Canvas as scheduled. They are usually due one week later or specified otherwise. One day automatic grace period. Second day late penalty -25%, later no credit.

# Exam rules

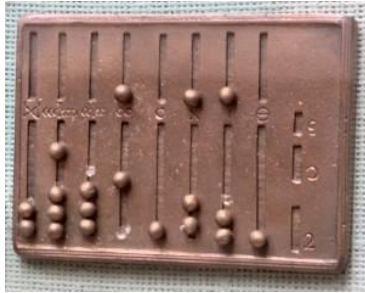
- There will be two midterm exams and one final exam.
- Students should complete the exam independently. No talk and collaboration are allowed.
- Closed book, cheat sheet may be allowed.
- No electronic devices except basic calculators will be allowed to use.
- Random quizzes are open book, but no cheating
- Any suspicious violation of the honor code will be reported to the honor council.

# Tentative schedule: (subject to change)

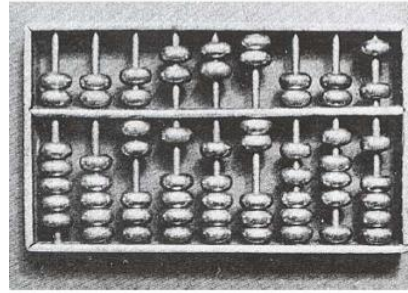
Week	Date	Lecture Topics	Homework
1	May 13	Introduction to solids, crystal structures	
	May 15	Introduction to quantum mechanics	HW1
2	May 20	Introduction to quantum mechanics	
	May 22	Energy band	HW2
	May 24	Energy band	
3	May 27	DOS and Fermi distribution	
	May 29	DOS and Fermi distribution	HW3
4	Jun. 3	Carrier and transport	
	Jun. 5	Carrier and transport	HW4
	Jun. 7	No Lecture, National Holiday	
5	Jun. 10	Carrier and transport	
	Jun. 12	No Lecture, Midterm Exam 1	HW5
6	Jun. 17	Carrier and transport	
	Jun. 19	PN junction	HW6
	Jun. 21	PN junction	
7	Jun. 24	PN junction	
	Jun. 26	PN junction	HW7
8	Jul. 1	PN junction	
	Jul. 3	BJT	
	Jul. 5	Schottky diode	HW8
9	Jul. 8	Lecture will be rescheduled due to time conflict	
	Jul. 10	Lecture will be rescheduled due to time conflict	
10	Jul. 15	No Lecture, Midterm Exam 2	
	Jul. 17	MOS Capacitor	HW9
	Jul. 19	MOS Capacitor	
11	Jul. 22	MOS Capacitor	
	Jul. 24	MOSFET	HW10
12	Jul. 29	MOSFET	
	Jul. 31	MOSFET	
	Aug. 2	MOSFET	
13	Aug. 9	No Lecture, Final Exam	

# Semiconductor Devices

## ■ The abacus, ancient digital memory



Roman Abacus (ca. 200BC)



Chinese Abacus (ca. 190AD)

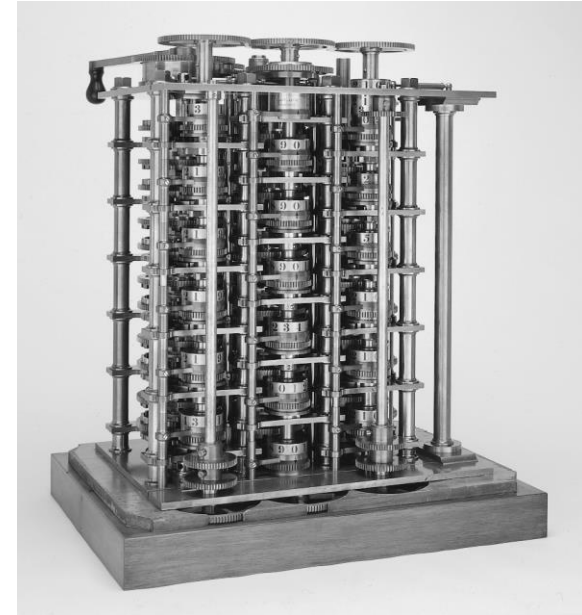
- Information represented in digital form
- Each rod is a decimal digit (units, tens, etc.)
- Can store information, and do calculation

## ■ An early mechanical computer

- The Babbage difference engine, 1832
- 25,000 parts



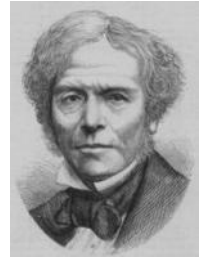
Charles Babbage  
(Wikipedia)



- Ohm's law:  $V = I \times R$ 
  - Georg Ohm, 1827



- Semiconductors are not metals
  - Semiconductor resistance decreases with temperature
  - Michael Faraday, 1834



- Discovery of the electron
  - J.J. Thomson, measured only charge/mass ratio, 1897
  - “To the electron, may it never be of any use to anybody.” – J.J. Thomson's favorite toast.

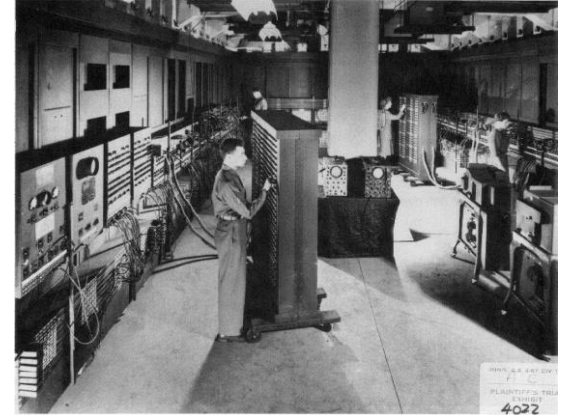


- Measuring the electron charge:  $1.6 \times 10^{-19} \text{ C}$ 
  - Robert Millikan, oil drops, 1909



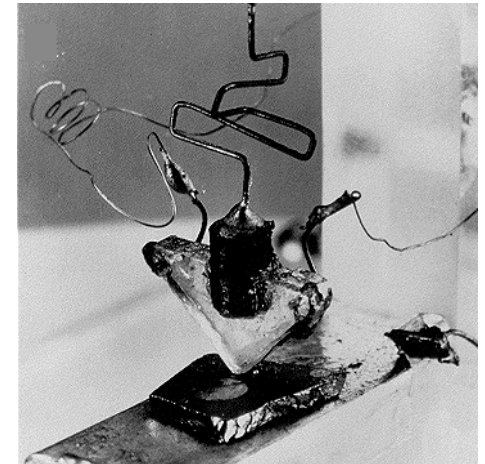
- ENIAC: The first electronic computer (1946)
  - 30 tons, including ~20,000 vacuum tubes, relays
  - Punch card inputs, ~5 kHz speed
  - It failed ~every five days

*Note: ILLIAC @ UIUC  
5 tons, 2800 vacuum tubes  
64k memory (1952)*



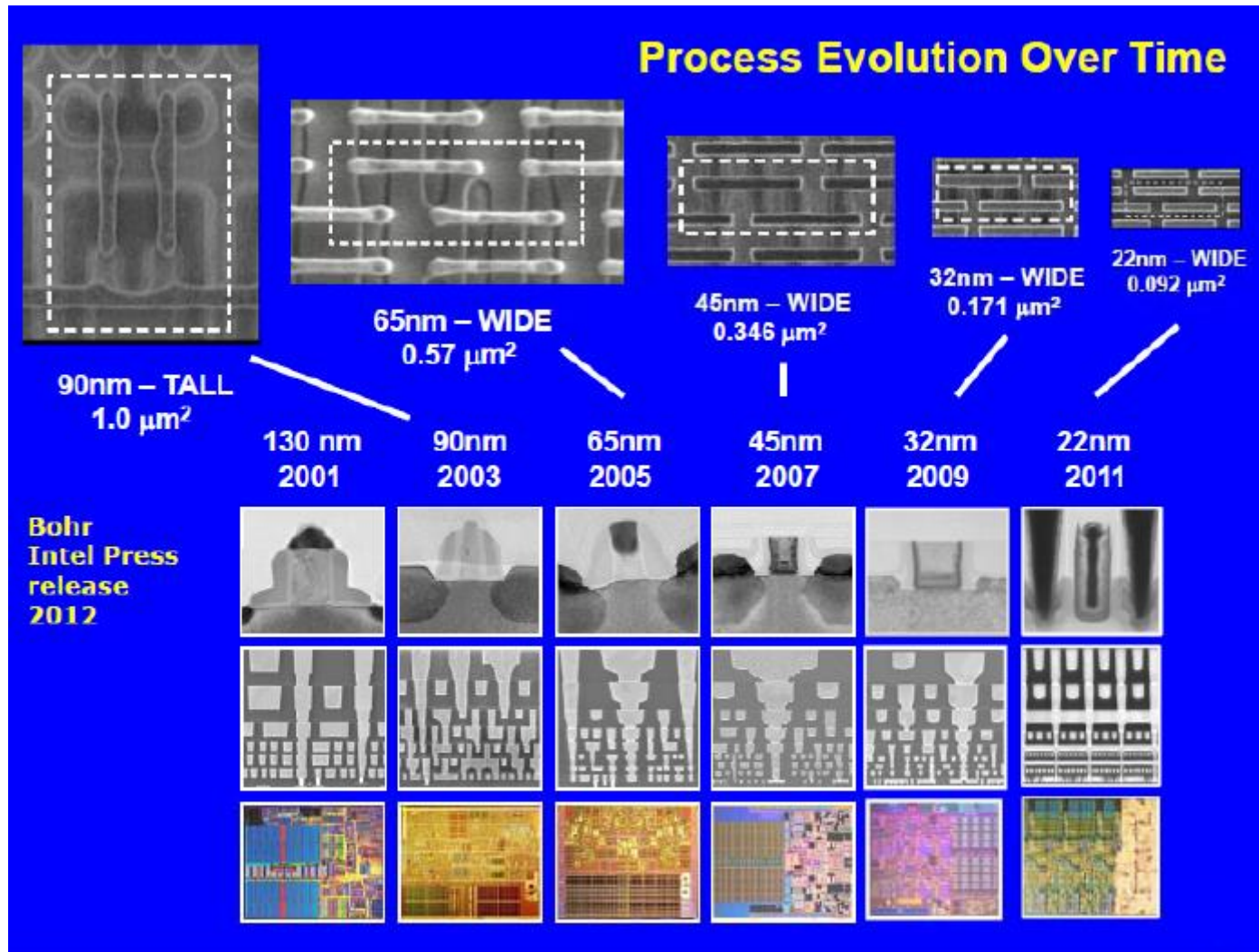
- Modern age begins in 1947:
  - The first semiconductor transistor
  - AT&T Bell Labs, Dec 1947
  - J. Bardeen, W. Brattain, W. Shockley
  - Germanium base, gold foil contacts

*Note: ILLIAC II @ UIUC  
Built with discrete transistors (1962)*



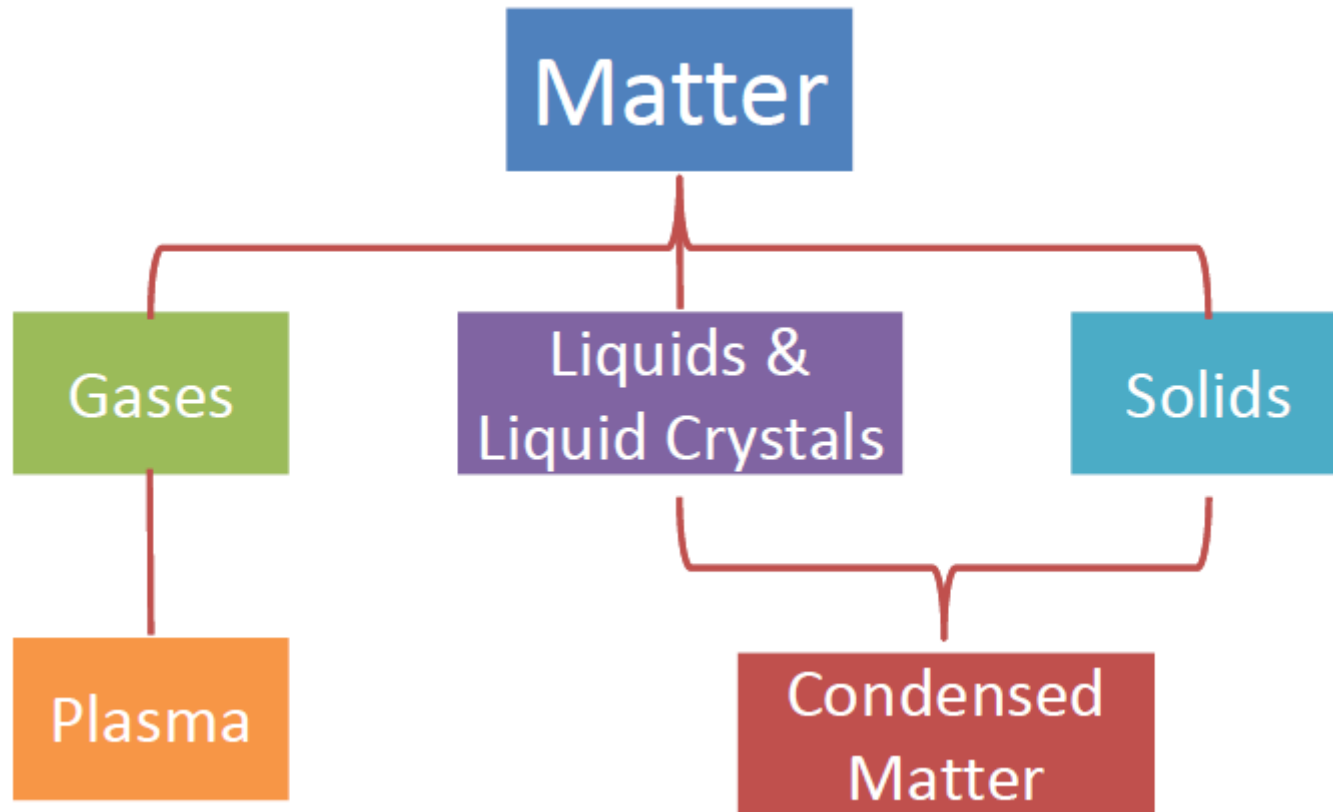


# Semiconductor processing



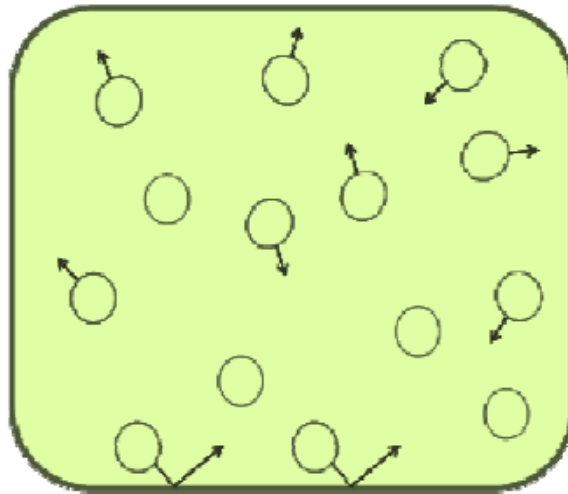
# Introduction to solids

# States, phases of matter



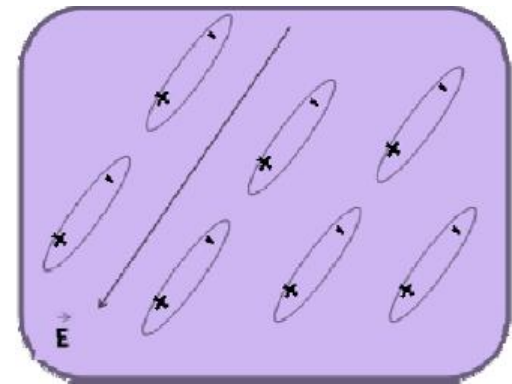
# Gases

- **Gases** have atoms or molecules that do not bond to one another in a range of pressure, temperature & volume.
- These molecules haven't any particular order & move freely within a container.



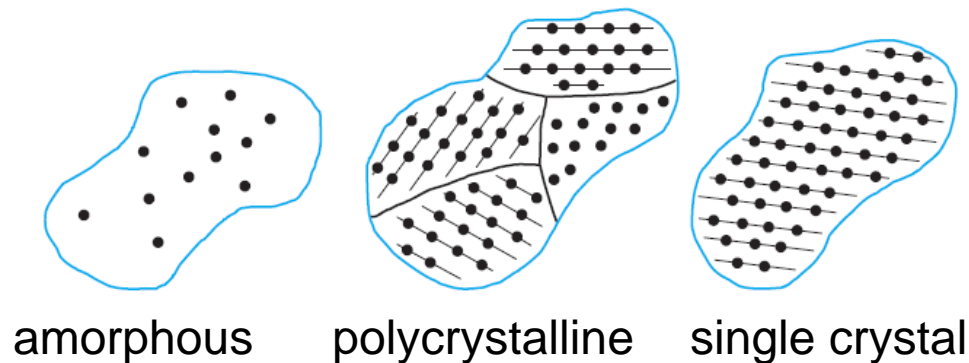
# Liquids & liquid crystals

- Similar to gases, **Liquids** have no atomic/molecular order & they assume the shape of their containers.
- Applying low levels of thermal energy can easily break the existing weak bonds.
- **Liquid Crystals** have mobile molecules, but a type of long range order can exist; the molecules have a permanent dipole. Applying an electric field rotates the dipole & establishes order within the collection of molecules.



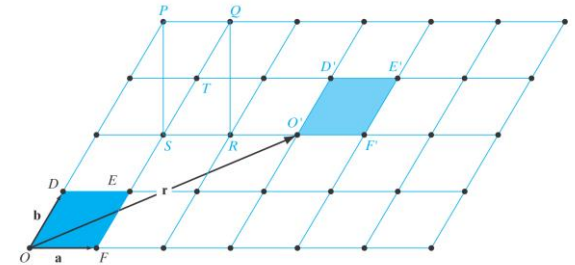
# Solids

- **Solids** consist of atoms or molecules *undergoing thermal motion* about their equilibrium positions, which are at *fixed points* in space.
- Solids can be amorphous, polycrystalline, or single crystal.

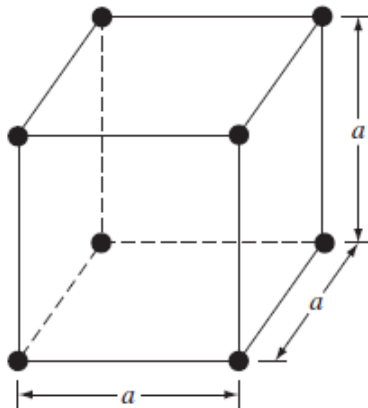


- Solids (at a given temperature, pressure, volume) have stronger interatomic bonds than liquids.
- So, solids require more energy to break the interatomic bonds than liquids.

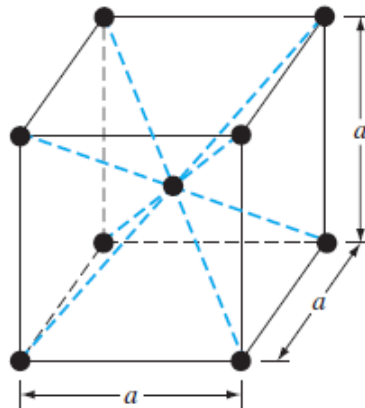
- The periodic lattice
  - Unit cell: can reproduce the crystal
  - Primitive cell: the smallest unit cell



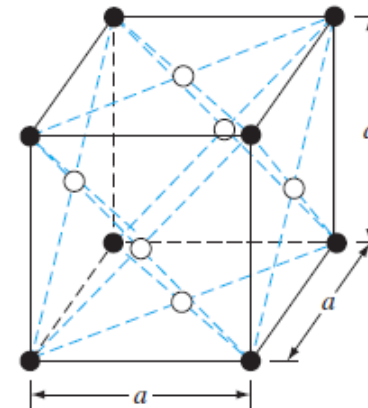
- Stuffing atoms into unit cells:



Simple cubic

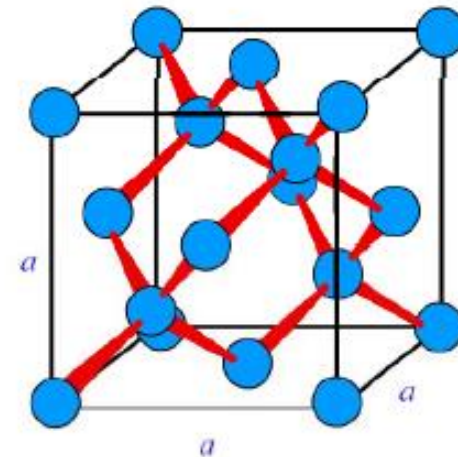
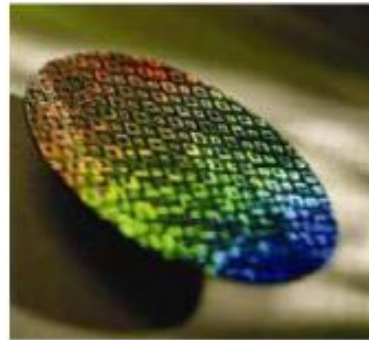
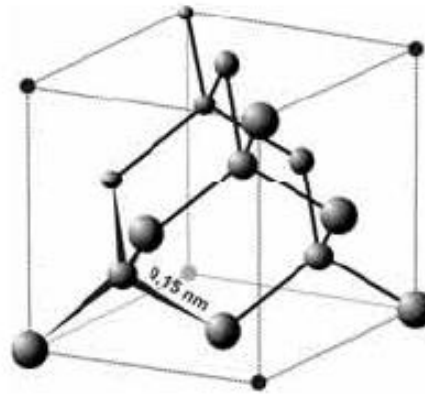
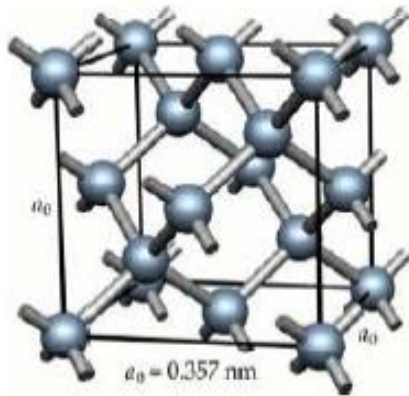


Body-centered  
cubic



Face-centered  
cubic

# Diamond structure – a special cubic



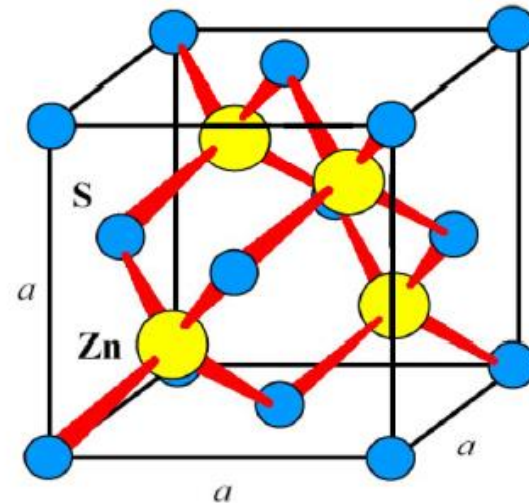


# The Silicon lattice:

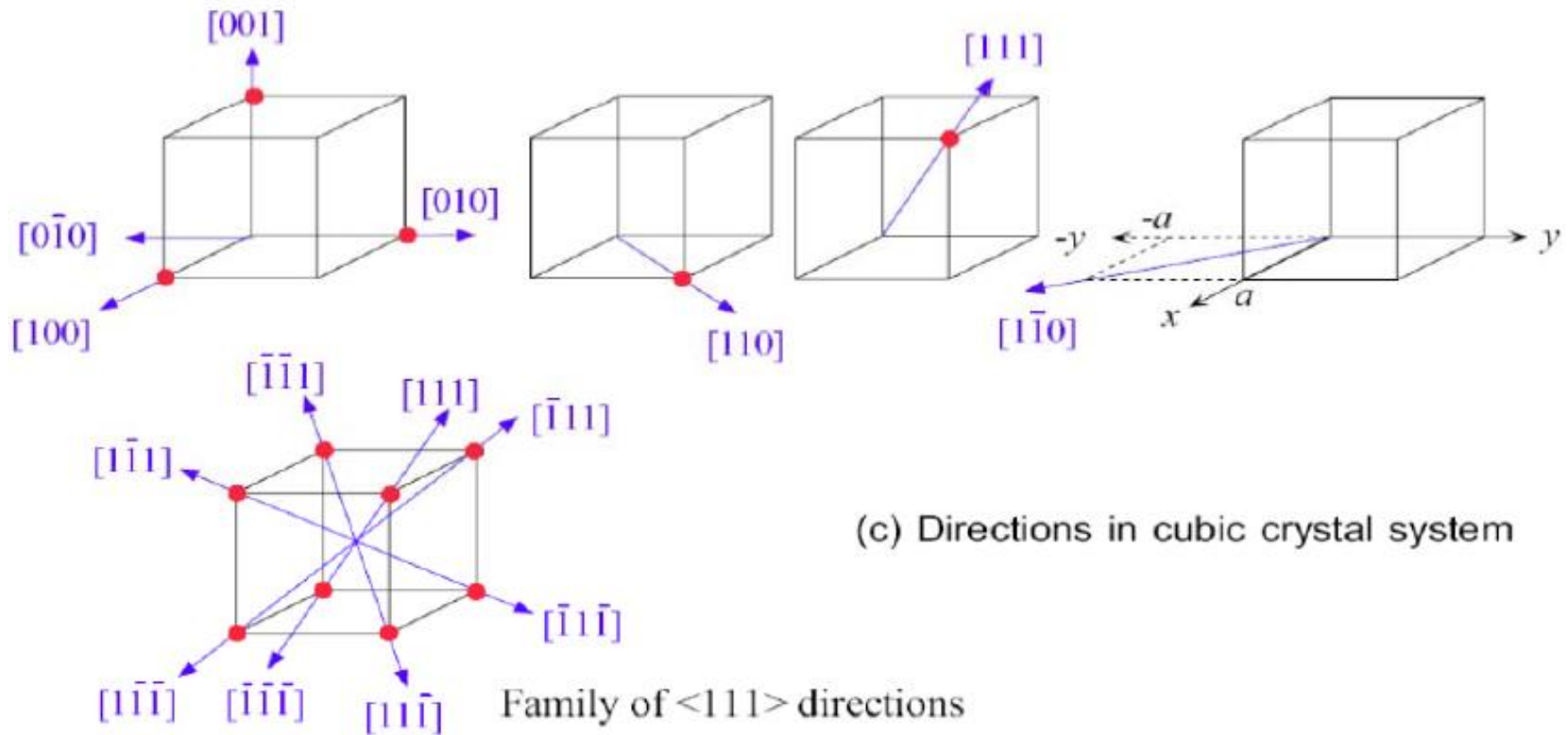
- “Diamond lattice”
- Si atom: 14 electrons occupying lowest 3 energy levels:
  - 1s, 2s, 2p orbitals filled by 10 electrons
  - 3s, 3p orbitals filled by 4 electrons
- Each Si atom has four neighbors
- Any atom within the diamond structure will have four nearest neighboring atoms
- The diamond structure refers to the particular lattice in which all atoms are of the same species, such as silicon or germanium
- How many atoms per unit cell?

# Zinc blende lattice

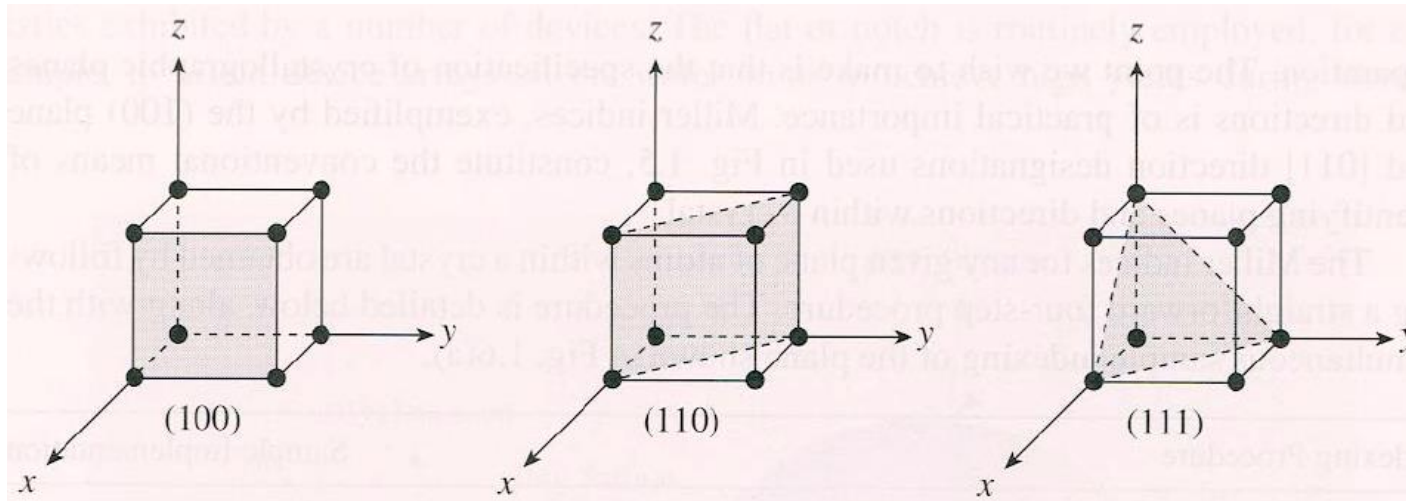
- The Zinc blende is diamond crystal structure, w/ switching atoms
- Two intercalated fcc lattices
- Many important compound crystal
- AlN, AlAs, GaAs, GaN, GaP, GaSb, InAs, InP, InSb, ZnS, ZnTe.



# ■ Crystallographic notation



# ■ Crystallographic planes



## Miller Indices

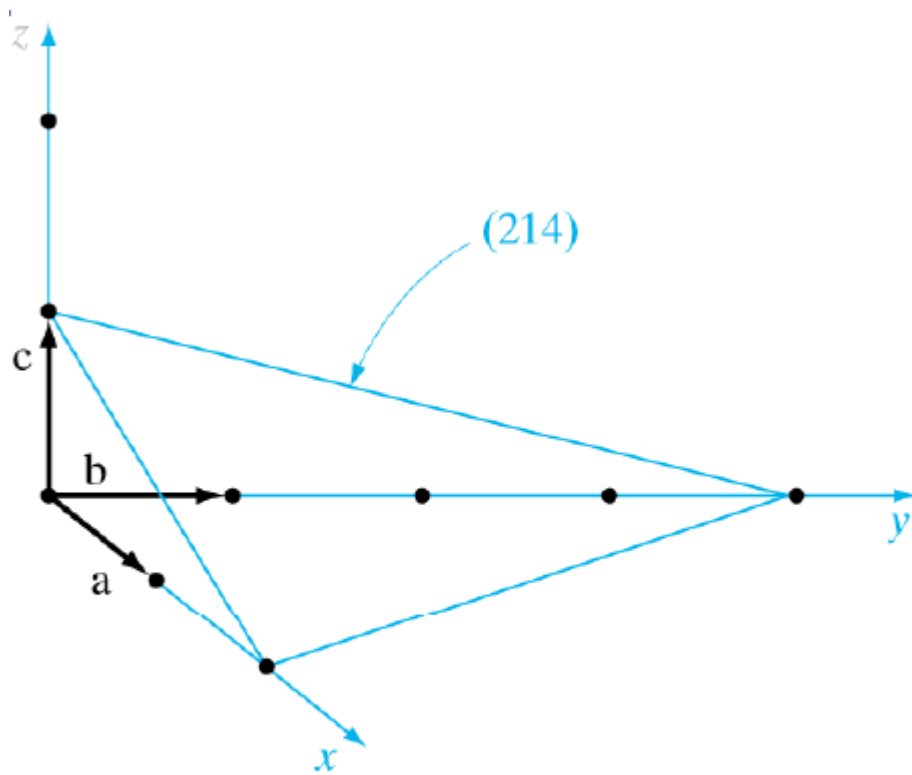
(Intercept values are in multiples of the lattice constant;  $h$ ,  $k$  and  $l$  are reduced to 3 integers having the same ratio.)

Notation	Interpretation
$(h\ k\ l)$	crystal plane
$\{h\ k\ l\}$	equivalent planes
$[h\ k\ l]$	crystal direction
$\langle h\ k\ l \rangle$	equivalent directions

**$h$ : inverse  $x$ -intercept of plane**

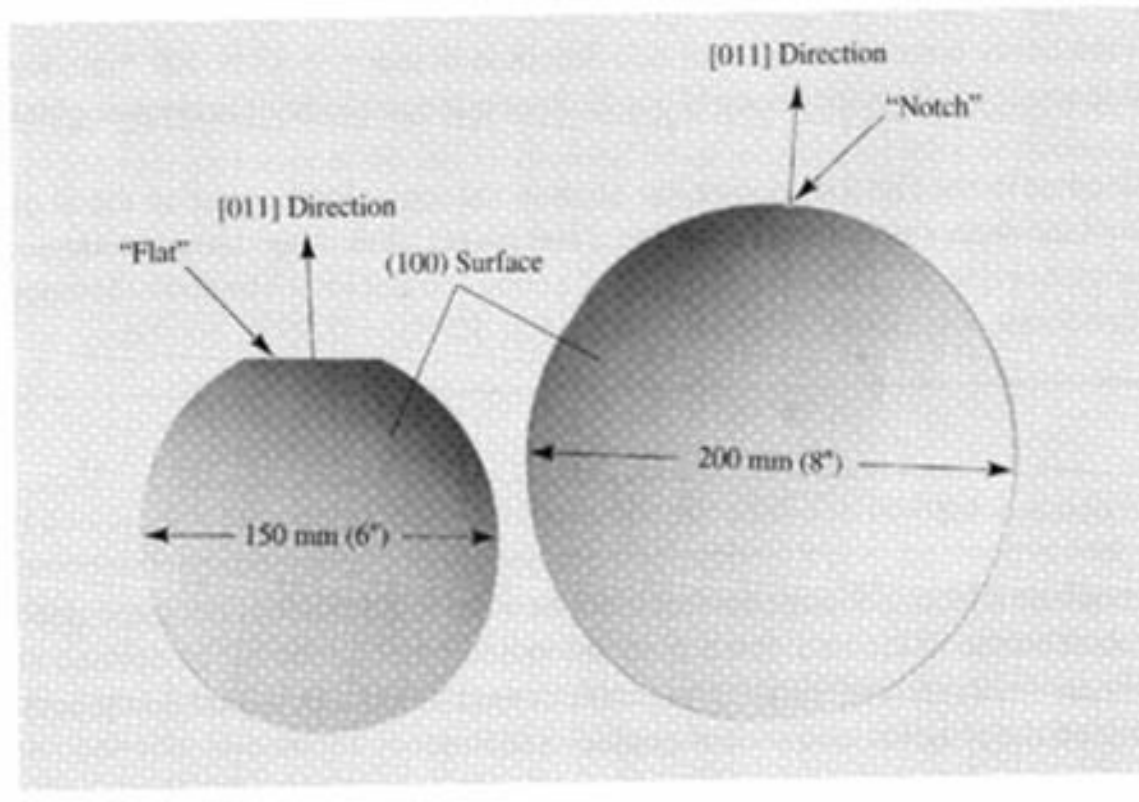
**$k$ : inverse  $y$ -intercept of plane**

**$l$ : inverse  $z$ -intercept of plane**

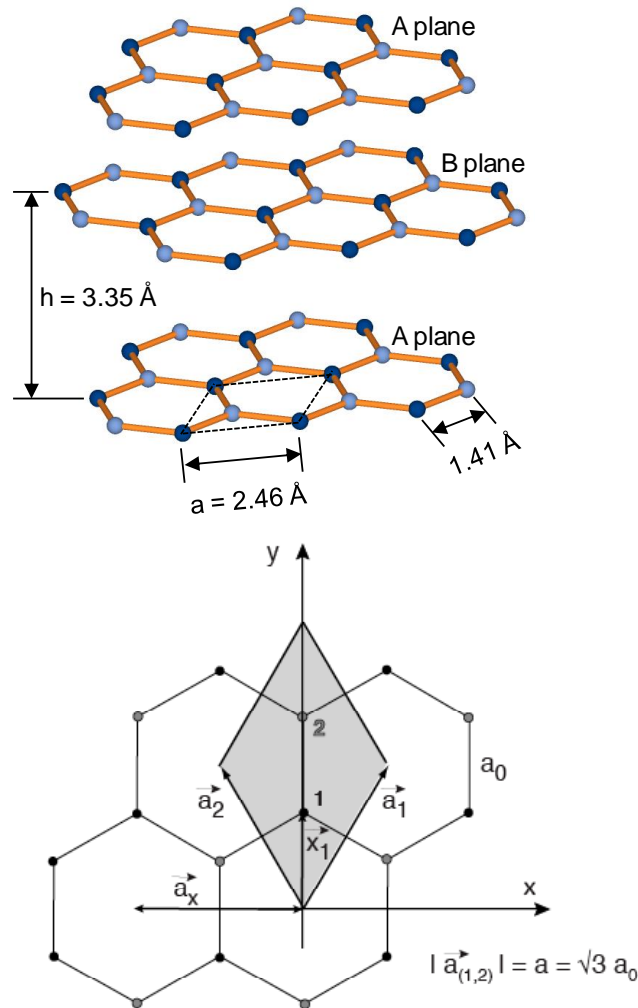


A  $(214)$  crystal plane.

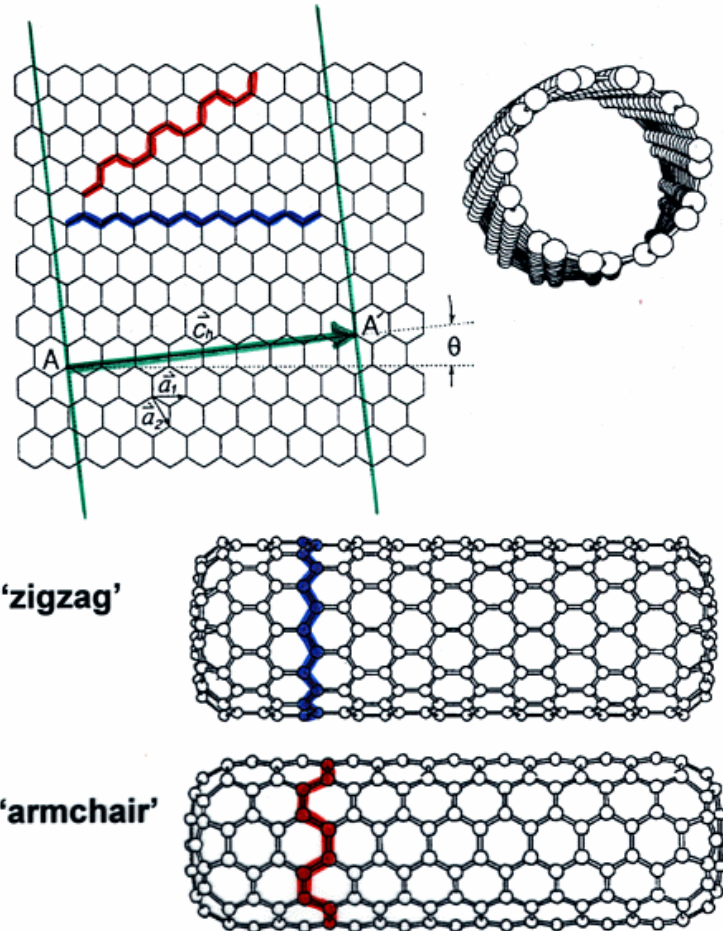
- Si wafers usually cut along  $\{100\}$  plane with a notch or flat side to orient the wafer during fabrication



- Graphite (~pencil lead) = parallel sheets of graphene
- Carbon nanotube = rolled up sheet of graphene



Various types of nanotubes





# The Scale of Things – Nanometers and More



## Things Natural



Dust mite  
200  $\mu\text{m}$

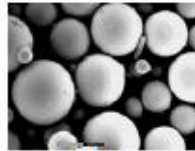


Human hair  
~60-120  $\mu\text{m}$  wide

Red blood cells  
(~7-8  $\mu\text{m}$ )



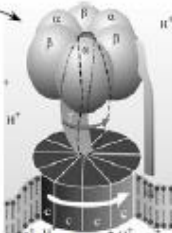
Ant  
~5 mm



Fly ash  
~10-20  $\mu\text{m}$



~10 nm diameter



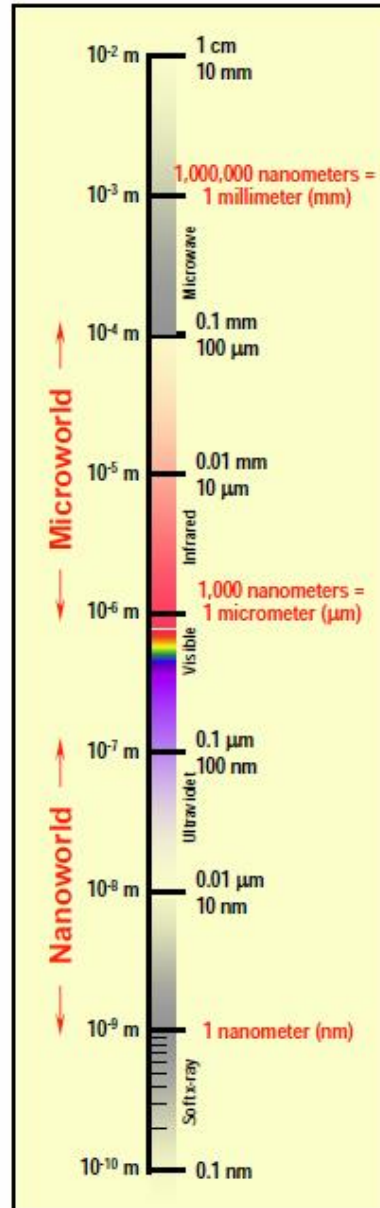
ATP synthase



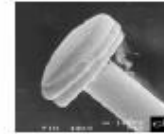
DNA  
~2-1/2 nm diameter



Atoms of silicon  
spacing 0.078 nm



## Things Manmade



Head of a pin  
1-2 mm

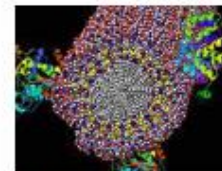
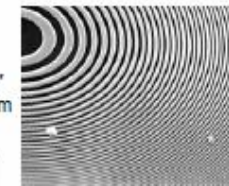


MicroElectroMechanical (MEMS) devices  
10-100  $\mu\text{m}$  wide

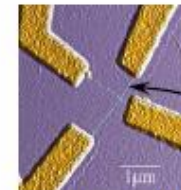


Pollen grain  
Red blood cells

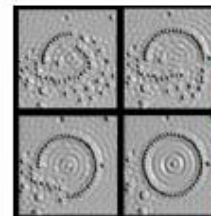
Zone plate x-ray "lens"  
Outer ring spacing ~35 nm



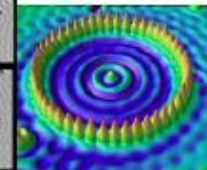
Self-assembled,  
Nature-inspired structure  
Many 10s of nm



Nanotube electrode

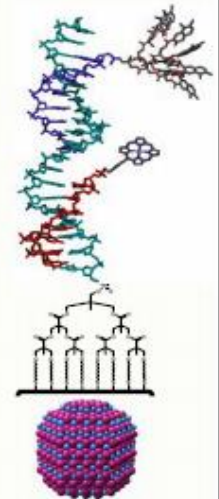


Quantum corral of 48 iron atoms on copper surface  
positioned one at a time with an STM tip  
Corral diameter 14 nm

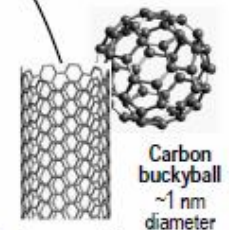


Carbon nanotube  
~1.3 nm diameter

### The Challenge



Fabricate and combine  
nanoscale building  
blocks to make useful  
devices, e.g., a  
photosynthetic reaction  
center with integral  
semiconductor storage.



Carbon buckyball  
~1 nm  
diameter

Office of Basic Energy Sciences  
Office of Science, U.S. DOE  
Version 05-05-06, final